## **ASSP**

# Single Serial Input PLL Frequency Synthesizer On-chip 2.0 GHz Prescaler

# MB15E05SL

#### **■ DESCRIPTION**

The Fujitsu Microelectronics MB15E05SL is a serial input Phase Locked Loop (PLL) frequency synthesizer with a 2.0 GHz prescaler. The 2.0 GHz prescaler has a dual modulus division ratio of 64/65 or 128/129 enabling pulse swallowing operation.

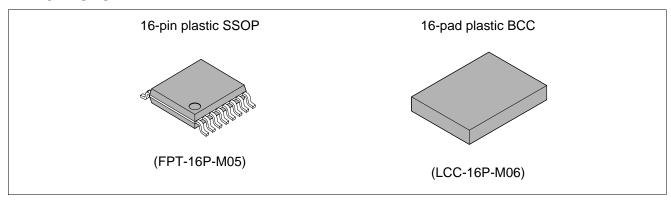
The supply voltage range is between 2.4 V and 3.6 V. The MB15E05SL uses the latest BiCMOS process, as a result the supply current is typically 3.0 mA at 2.7 V. A refined charge pump supplies well-balanced output currents of 1.5 mA and 6 mA. The charge pump current is selectable by serial data.

MB15E05SL is ideally suited for wireless mobile communications, such as GSM (Global System for Mobile Communications) and PCS.

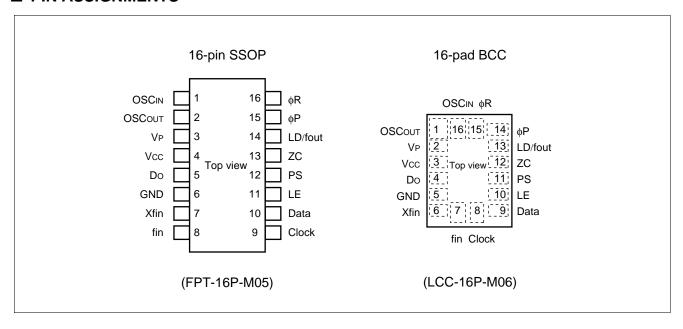
#### **■ FEATURES**

- · High frequency operation: 2.0 GHz max
- Low power supply voltage: Vcc = 2.4 to 3.6 V
- Ultra Low power supply current: Icc = 3.0 mA typ. (Vcc = Vp = 2.7 V, Ta = +25°C, in locking state)
  Icc = 3.5 mA typ. (Vcc = Vp = 3.0 V, Ta = +25°C, in locking state)
- Direct power saving function: Power supply current in power saving mode
  - Typ.  $0.1 \,\mu\text{A}$  (Vcc = Vp =  $3.0 \,\text{V}$ , Ta =  $+25 \,^{\circ}\text{C}$ ), Max.  $10 \,\mu\text{A}$  (Vcc = Vp =  $3.0 \,\text{V}$ )
- Dual modulus prescaler: 64/65 or 128/129
- Serial input 14-bit programmable reference divider: R = 3 to 16,383
- · Serial input programmable divider consisting of:
  - Binary 7-bit swallow counter: 0 to 127
  - Binary 11-bit programmable counter: 3 to 2,047
- Software selectable charge pump current
- On-chip phase control for phase comparator
- Operating temperature: Ta = −40 to +85°C
- Pin compatible with MB15E05, MB15E05L

### **■ PACKAGES**



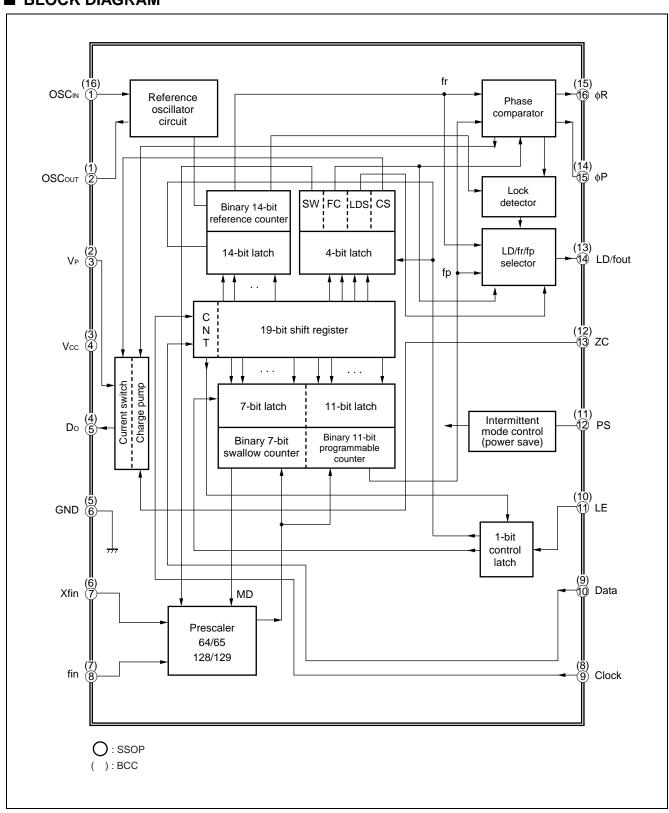
### **■ PIN ASSIGNMENTS**



### **■ PIN DESCRIPTIONS**

Pin	no.	Pin		<b>5</b>
SSOP	ВСС	name	I/O	Descriptions
1	16	OSCIN	l	Programmable reference divider input. Connection to a TCXO.
2	1	OSCout	0	Oscillator output.
3	2	VP	-	Power supply voltage input for the charge pump.
4	3	Vcc	-	Power supply voltage input.
5	4	Do	0	Charge pump output. Phase of the charge pump can be selected via programming of the FC bit.
6	5	GND	_	Ground.
7	6	Xfin	ļ	Prescaler complementary input, which should be grounded via a capacitor.
8	7	fin	I	Prescaler input. Connection to an external VCO should be done via AC coupling.
9	8	Clock	I	Clock input for the 19-bit shift register. Data is shifted into the shift register on the rising edge of the clock. (Open is prohibited.)
10	9	Data	ļ	Serial data input using binary code. The last bit of the data is a control bit. (Open is prohibited.)
11	10	LE	I	Load enable signal input. (Open is prohibited.) When LE is set high, the data in the shift register is transferred to a latch according to the control bit in the serial data.
12	11	PS	I	Power saving mode control. This pin must be set at "L" at Power-ON. (Open is prohibited.) PS = "H"; Normal mode PS = "L"; Power saving mode
13	12	ZC	I	Forced high-impedance control for the charge pump (with internal pull up resistor.) ZC = "H"; Normal Do output. ZC = "L"; Do becomes high impedance.
14	13	LD/fout	0	Lock detect signal output (LD)/phase comparator monitoring output (fout). The output signal is selected via programming of the LDS bit.  LDS = "H"; outputs fout (fr/fp monitoring output)  LDS = "L"; outputs LD ("H" at locking, "L" at unlocking.)
15	14	φР	0	Phase comparator N-channel open drain output for an external charge pump. Phase can be selected via programming of the FC bit.
16	15	φR	0	Phase comparator CMOS output for an external charge pump. Phase can be selected via programming of the FC bit.

### **■ BLOCK DIAGRAM**



### ■ ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Condition	Ra	ting	Unit	Remark
Parameter	Symbol	Condition	Min.	Max.	Offic	Remark
Power supply voltage	Vcc	_	-0.5	4.0	V	
Fower supply voltage	VP	_	Vcc	6.0	V	
Input voltage	Vı	_	-0.5	Vcc +0.5	V	
Output voltage	Vo	Except Do	GND	Vcc	V	
Output voltage	Vo	Do	GND	VP	V	
Storage temperature	Tstg	_	<b>-</b> 55	+125	°C	

WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.

### ■ RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol		Value	Unit	Remark	
raiailletei	Symbol	Min.	Тур.	Max.	Oill	Remark
Dower aupply voltage	Vcc	2.4	3.0	3.6	V	
Power supply voltage	VP	Vcc	-	5.5	V	
Input voltage	Vı	GND	_	Vcc	V	
Operating temperature	Ta	-40	_	+85	°C	

WARNING: The recommended operating conditions are required in order to ensure the normal operation of the semiconductor device. All of the device's electrical characteristics are warranted when the device is operated within these ranges.

Always use semiconductor devices within their recommended operating condition ranges. Operation outside these ranges may adversely affect reliability and could result in device failure.

No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their representatives beforehand.

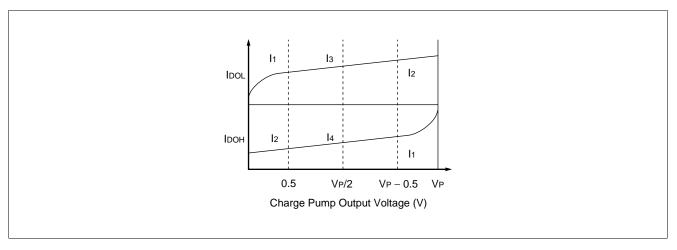
### **■ ELECTRICAL CHARACTERISTICS**

 $(Vcc = 2.4 \text{ to } 3.6 \text{ V}, Ta = -40 \text{ to } +85^{\circ}\text{C})$ 

Dovernator						Value		11	
Parameter		Symbol	Con	dition	Min.	Тур.	Max.	Unit	
Power supply current*1		Icc	fin = 2000 MHz, (Vcc = V <sub>P</sub> = 3.0	_	3.0 (3.5)	-	mA		
Power saving current		<b>I</b> PS	ZC = "H" or ope	_	0.1*2	10	μΑ		
	fin	fin		_	100	_	2000	MHz	
Operating frequency	OSCIN	fosc		_	3	_	40	MHz	
Input sensitivity	fin*3	Pfin	$50 \Omega$ system (Refer to the me circuit.)	easurement	-15	_	+2	dBm	
	OSC <sub>IN*3</sub>	Vosc		_	0.5	-	Vcc	Vp-p	
"H" level input voltage	Data,	Vін		_	$Vcc \times 0.7$	_	_		
"L" level input voltage	Clock, LE, PS, ZC	VIL		_	_	Vcc × 0.3	V		
"H" level input current	Data,	I <sub>IH</sub> *4		_	-1.0	_	+1.0		
"L" level input current	Clock, LE, PS	Iı∟*4		_	-1.0	_	+1.0	μΑ	
"H" level input current		Іін		_	0	_	+100		
"L" level input current	OSCIN	Iı∟*4		_	-100	_	0	μΑ	
"H" level input current		I <sub>IH</sub> *4		_	-1.0	_	+1.0		
"L" level input current	ZC	Iı∟*4	Pull up input		-100	_	0	μΑ	
"L" level output voltage	φР	Vol	Open drain outp	out	_	_	0.4	V	
"H" level output voltage	φR,	Vон	Vcc = Vp = 3.0 \	/, Iон = -1 mA	Vcc - 0.4	_	_		
"L" level output voltage	LD/fout	Vol	Vcc = Vp = 3.0 \	/, IoL = 1 mA	_	_	0.4	V	
"H" level output voltage	_	V <sub>DOH</sub>	Vcc = Vp = 3.0 \	$I_{\rm DOH} = -0.5  \text{mA}$	V <sub>P</sub> - 0.4	_	_	,,	
"L" level output voltage	Do	V <sub>DOL</sub>	Vcc = Vp = 3.0 \	/, I <sub>DOL</sub> = 0.5 mA	_	_	0.4	V	
High impedance cutoff current	Do	loff	$V_{CC} = V_P = 3.0 \ V_{OFF} = 0.5 \ V \text{ to} \ V_{CC}$	/, Vp − 0.5 V	_	-	2.5	nA	
"L" level output current	φР	loL	Open drain outp	out	1.0	_	_	mA	
"H" level output current	φR,	Іон		_	_	_	-1.0		
"L" level output current	LD/fout	loL		_	1.0	_	_	mA	
41111				CS bit = "H"	_	-6.0	_		
"H" level output current	Б.	IDOH*4	$V_{CC} = 3 \text{ V},$ $V_P = 3 \text{ V},$	CS bit = "L"	_	-1.5	_		
((1)   1   1   1   1   1   1   1   1   1	Do		V <sub>DO</sub> = V <sub>P</sub> /2, Ta = +25°C	CS bit = "H"	_	6.0	_	mA	
"L" level output current		DOL	ia = +25°C	CS bit = "L"	_	1.5	_		
	IDOL/IDOH	<b>І</b> ромт*5	V <sub>DO</sub> = V <sub>P</sub> /2	,	_	3	_	%	
Charge pump current rate	vs V <sub>DO</sub>	IDOVD*6	0.5 V ≤ V <sub>DO</sub> ≤ V <sub>I</sub>	P − 0.5 V	_	10	_	%	
1.4.5	vs Ta	IDOTA*7	– 40°C ≤ Ta ≤ +	85°C	_	10	_	%	

- \*1: Conditions; fosc = 12 MHz, Ta = +25°C, in locking state.
- $V_{CC} = V_P = 3.0 \text{ V}$ , fosc = 12.8 MHz, Ta = +25°C, in power saving mode
- \*3: AC coupling. 1000 pF capacitor is connected under the condition of min. operating frequency.
  \*4: The symbol "—" (minus) means direction of current flow.

- \*5:  $V_{CC} = V_P = 3.0 \text{ V}$ ,  $T_a = +25^{\circ}\text{C} \left( \left| I_3 \right| \left| I_4 \right| \right) / \left[ \left( \left| I_3 \right| + \left| I_4 \right| \right) / 2 \right] \times 100(\%)$ \*6:  $V_{CC} = V_P = 3.0 \text{ V}$ ,  $T_a = +25^{\circ}\text{C} \left( \left| \left| I_2 \right| \left| I_1 \right| \right) / 2 \right] / \left[ \left( \left| I_1 \right| + \left| I_2 \right| \right) / 2 \right] \times 100(\%)$  (Applied to each IDOL, IDOH)
- \*7:  $V_{CC} = V_P = 3.0 \text{ V}, V_{DO} = V_P/2 \left( \frac{||DO(+85^{\circ}C) |DO(-40^{\circ}C)|}{2} \right) / \left( \frac{||DO(+85^{\circ}C) + |DO(-40^{\circ}C)|}{2} \right) \times 100(\%)$  (Applied to each IDOL, IDOH)



### **■ FUNCTIONAL DESCRIPTION**

### 1. Pulse Swallow Function

The divide ratio can be calculated using the following equation:

 $f_{VCO} = [(M \times N) + A] \times f_{OSC} \div R \quad (A < N)$ 

fvco : Output frequency of external voltage controlled oscillator (VCO)
 N : Preset divide ratio of binary 11-bit programmable counter (3 to 2,047)
 A : Preset divide ratio of binary 7-bit swallow counter (0 ≤ A ≤ 127)

fosc : Output frequency of the reference frequency oscillator

R : Preset divide ratio of binary 14-bit programmable reference counter (3 to 16,383)

M : Preset divide ratio of modulus prescaler (64 or 128)

### 2. Serial Data Input

Serial data is processed using the Data, Clock, and LE pins. Serial data controls the programmable reference divider and the programmable divider separately.

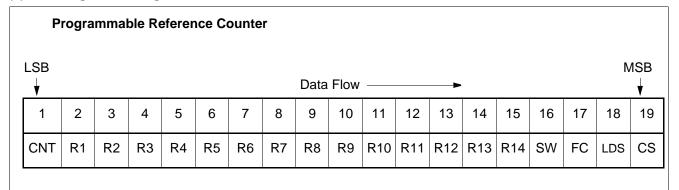
Binary serial data is entered through the Data pin.

One bit of data is shifted into the shift register on the rising edge of the Clock. When the LE signal pin is taken high, stored data is latched according to the control bit data as follows:

**Table 1. Control Bit** 

Control bit (CNT)	Destination of serial data
Н	For the programmable reference divider
L	For the programmable divider

#### (1) Shift Register Configuration



: Control bit CNT [Table 1] Table 2 R1 to R14 : Divide ratio setting bit for the programmable reference counter (3 to 16,383) SW : Divide ratio setting bit for the prescaler (64/65 or 128/129) [Table 5] FC : Phase control bit for the phase comparator [Table 8] LDS : LD/fout signal select bit [Table 7] : Charge pump current select bit CS [Table 6]

Note: Start data input with MSB first.

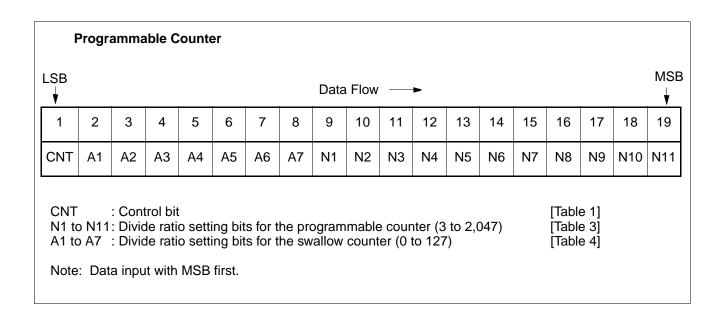


Table 2. Binary 14-bit Programmable Reference Counter Data Setting

Divide ratio(R)	R14	R13	R12	R11	R10	R9	R8	R7	R6	R5	R4	R3	R2	R1
3	0	0	0	0	0	0	0	0	0	0	0	0	1	1
4	0	0	0	0	0	0	0	0	0	0	0	1	0	0
		•	•	•	•					•				
16383	1	1	1	1	1	1	1	1	1	1	1	1	1	1

Note: Divide ratio less than 3 is prohibited.

Table 3. Binary 11-bit Programmable Counter Data Setting

Divide ratio(N)	N11	N10	N9	N8	N7	N6	N5	N4	N3	N2	N1
3	0	0	0	0	0	0	0	0	0	1	1
4	0	0	0	0	0	0	0	0	1	0	0
				•	•			•	•	•	
2047	1	1	1	1	1	1	1	1	1	1	1

Note: Divide ratio less than 3 is prohibited.

**Table 4. Binary 7-bit Swallow Counter Data Setting** 

Divide ratio(A)	<b>A7</b>	<b>A6</b>	<b>A</b> 5	<b>A4</b>	А3	A2	<b>A</b> 1
0	0	0	0	0	0	0	0
1	0	0	0	0	0	0	1
	•	•	•	•	•	•	•
127	1	1	1	1	1	1	1

**Table 5. Prescaler Data Setting** 

SW	Prescaler divide ratio
Н	64/65
L	128/129

**Table 6. Charge Pump Current Setting** 

CS	Current value
Н	±6.0 mA
L	±1.5 mA

Table 7. LD/fout Output Select Data Setting

LDS	LD/fout output signal
Н	fout signal
L	LD signal

### (2) Relation between the FC Input and Phase Characteristics

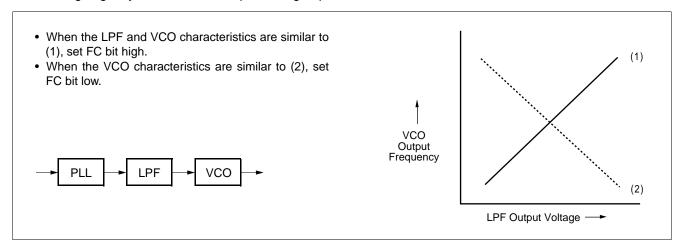
The FC bit changes the phase characteristics of the phase comparator. Both the internal charge pump output level (Do) and the phase comparator output ( $\phi$ R,  $\phi$ P) are reversed according to the FC bit. Also, the monitor pin (fout) output is controlled by the FC bit. The relationship between the FC bit and each of Do,  $\phi$ R, and  $\phi$ P is shown below.

Table 8. FC Bit Data Setting (LDS = "H")

		FC =	High		FC = Low				
	Do	φR	φР	LD/fout	Do	φR	φР	LD/fout	
fr > f₽	Н	L	L		L	Н	Z*		
fr < f₽	L	Н	Z*	fout = fr	Н	L	L	fout = fp	
fr = f <sub>P</sub>	Z*	L	Z*		Z*	L	Z*		

<sup>\*:</sup> High impedance

When designing a synthesizer, the FC pin setting depends on the VCO and LPF characteristics.



### 3. Do Output Control

Table 9. ZC Pin Setting

ZC pin	Do output		
Н	Normal output		
L	High impedance		

### 4. Power Saving Mode (Intermittent Mode Control Circuit)

Table 10. PS Pin Setting

PS pin	Status		
Н	Normal mode		
L	Power saving mode		

The intermittent mode control circuit reduces the PLL power consumption.

By setting the PS pin low, the device enters into the power saving mode, reducing the current consumption. See the Electrical Characteristics chart for the specific value.

The phase detector output, Do, becomes high impedance.

For the signal PLL, the lock detector, LD, remains high, indicating a locked condition.

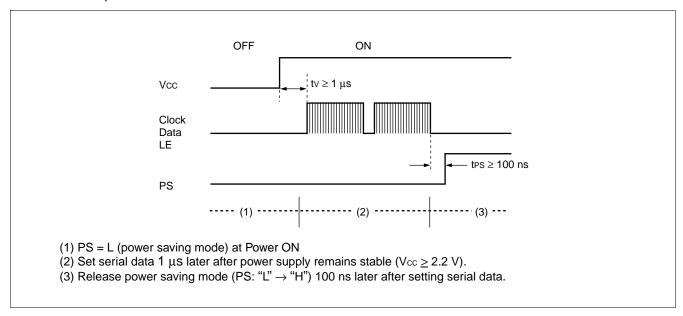
Setting the PS pin high, releases the power saving mode, and the device works normally.

The intermittent mode control circuit also ensures a smooth startup when the device returns to normal operation. When the PLL is returned to normal operation, the phase comparator output signal is unpredictable. This is because of the unknown relationship between the comparison frequency (fp) and the reference frequency (fr) which can cause a major change in the comparator output, resulting in a VCO frequency jump and an increase in lockup time.

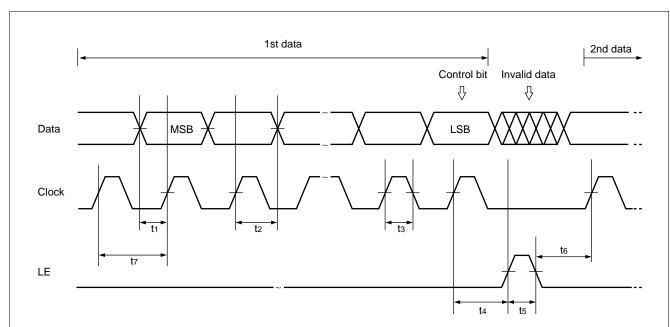
To prevent a major VCO frequency jump, the intermittent mode control circuit limits the magnitude of the error signal from the phase detector when it returns to normal operation.

Note: When power (Vcc) is first applied, the device must be in standby mode, PS = Low, for at least 1  $\mu$ s.

Note: • PS pin must be set "L" for Power-ON.



### ■ SERIAL DATA INPUT TIMING



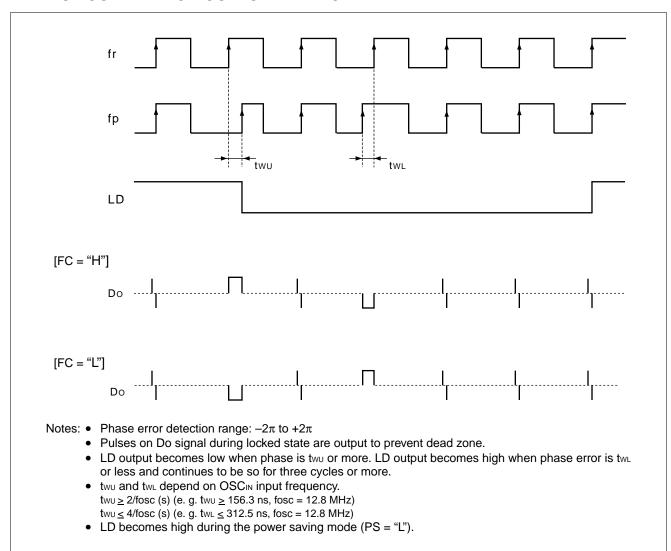
On the rising edge of the clock, one bit of data is transferred into the shift register.

Parameter	Min.	Тур.	Max.	Unit
<b>t</b> 1	20	_	_	ns
<b>t</b> 2	20	_	_	ns
t <sub>3</sub>	30	_	_	ns
t <sub>4</sub>	30	_	_	ns

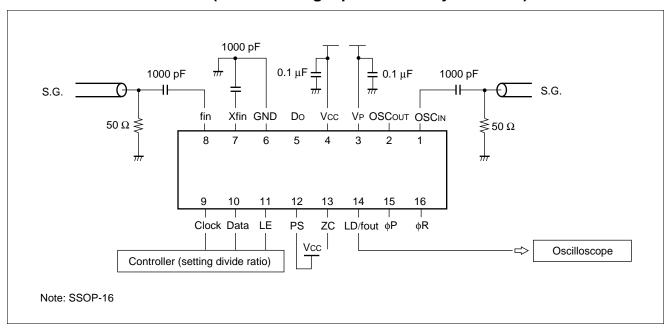
Parameter	Min.	Тур.	Max.	Unit
<b>t</b> 5	100	-	-	ns
<b>t</b> 6	20	1	-	ns
<b>t</b> 7	100	ı	ı	ns

Note: LE should be "L" when the data is transferred into the shift register.

### **■ PHASE COMPARATOR OUTPUT WAVEFORM**

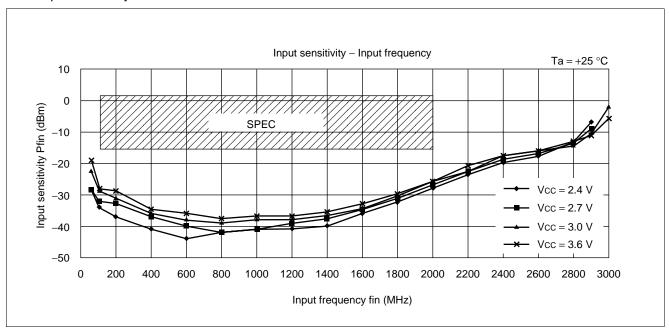


## ■ MEASURMENT CIRCUIT (for Measuring Input Sensitivity fin/OSC<sub>IN</sub>)

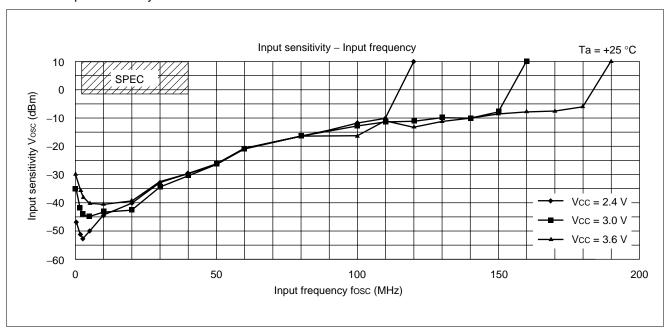


### **■ TYPICAL CHARACTERISTICS**

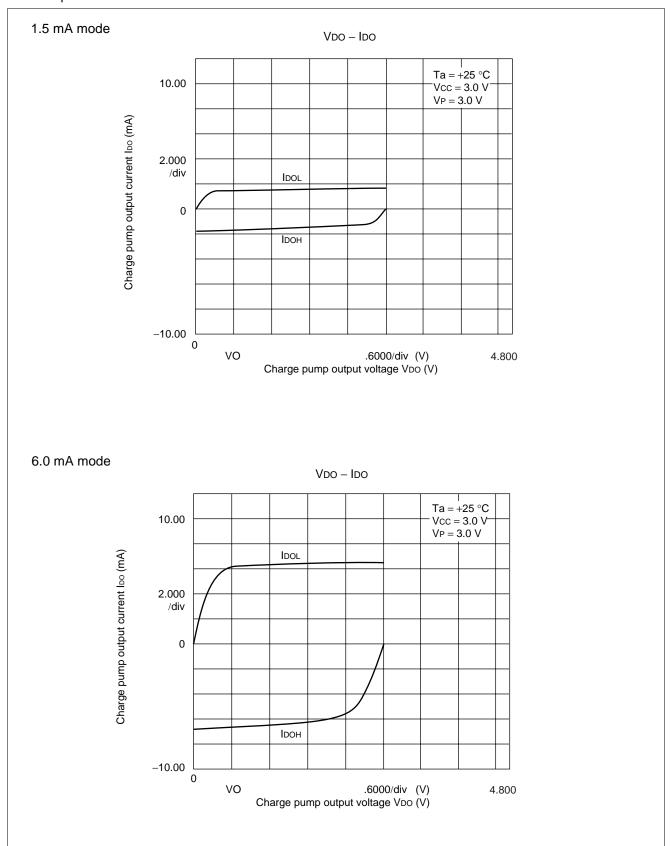
### 1. fin input sensitivity



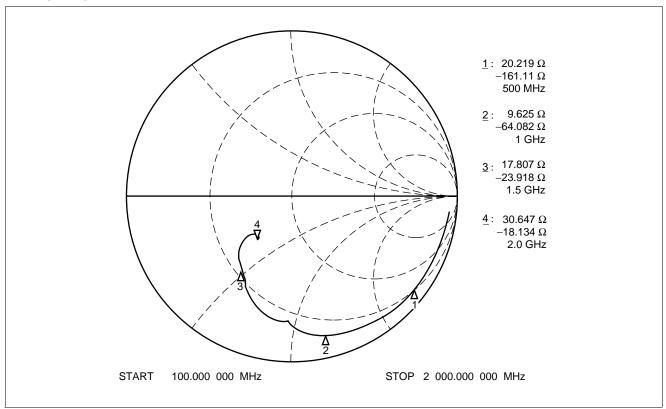
### 2. OSC<sub>IN</sub> input sensitivity



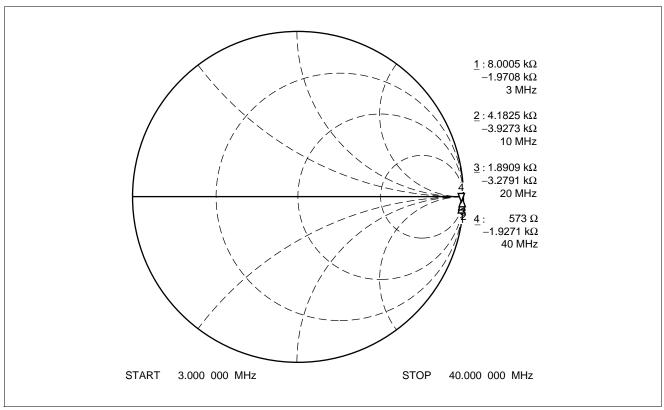
### 3. Do output current



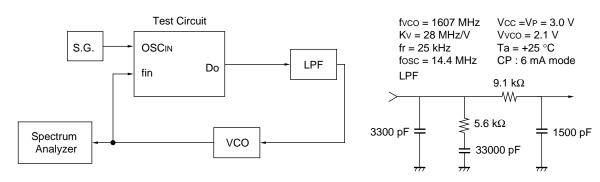
### 4. fin input impedance

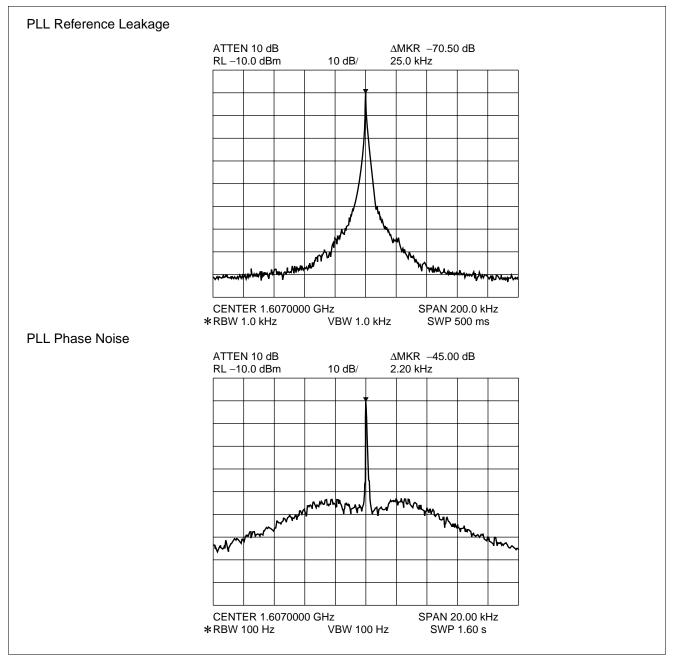


### 5. OSC<sub>IN</sub> input impedance

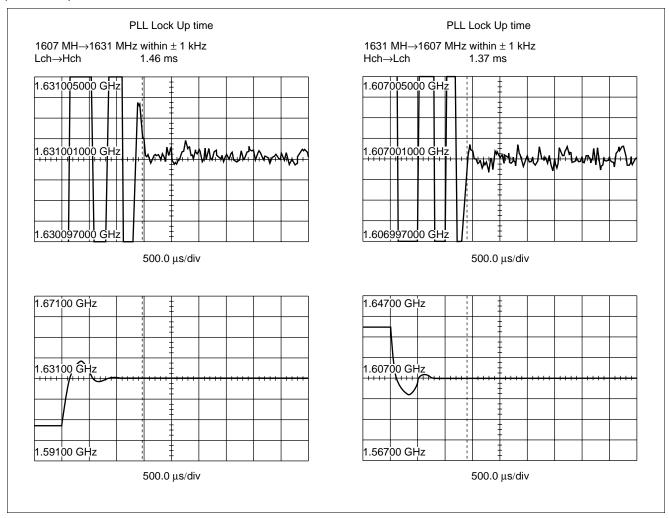


### **■ REFERENCE INFORMATION**

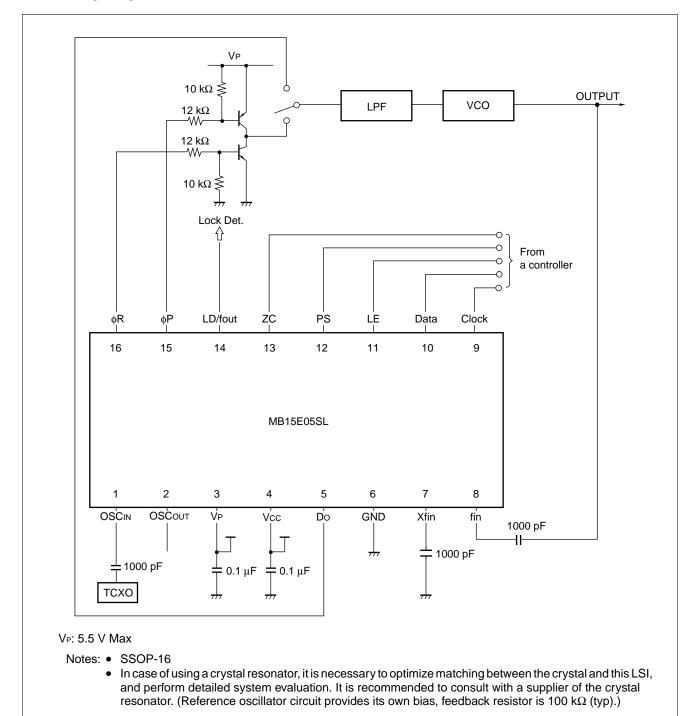




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### **■ APPLICATION EXAMPLE**



### **■ USAGE PRECAUTIONS**

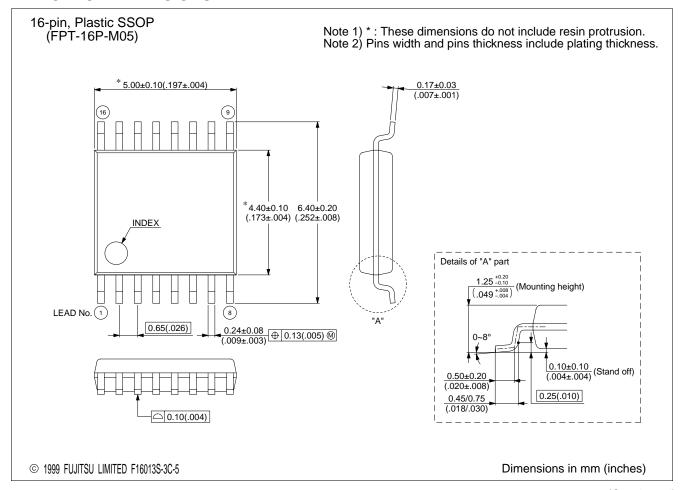
To protect against damage by electrostatic discharge, note the following handling precautions:

- -Store and transport devices in conductive containers.
- -Use properly grounded workstations, tools, and equipment.
- -Turn off power before inserting device into or removing device from a socket.
- -Protect leads with a conductive sheet when transporting a board-mounted device.

## **■** ORDERING INFORMATION

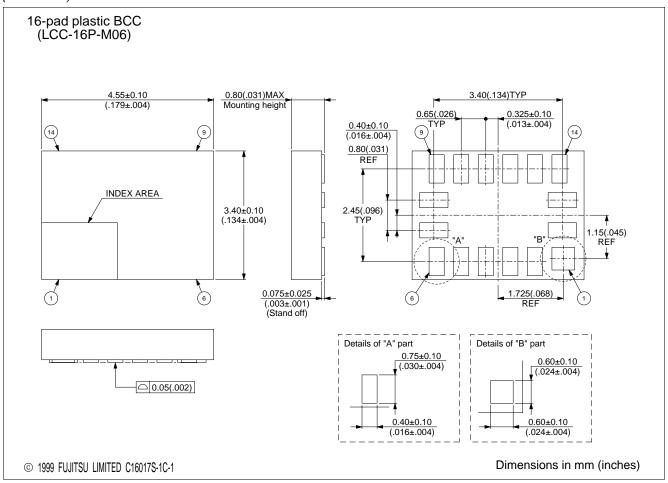
Part number	Package	Remarks
MB15E05SLPFV1	16-pin, Plastic SSOP (FPT-16P-M05)	
MB15E05SLPV1	16-pad, Plastic BCC (LCC-16P-M06)	

### **■ PACKAGE DIMENSIONS**

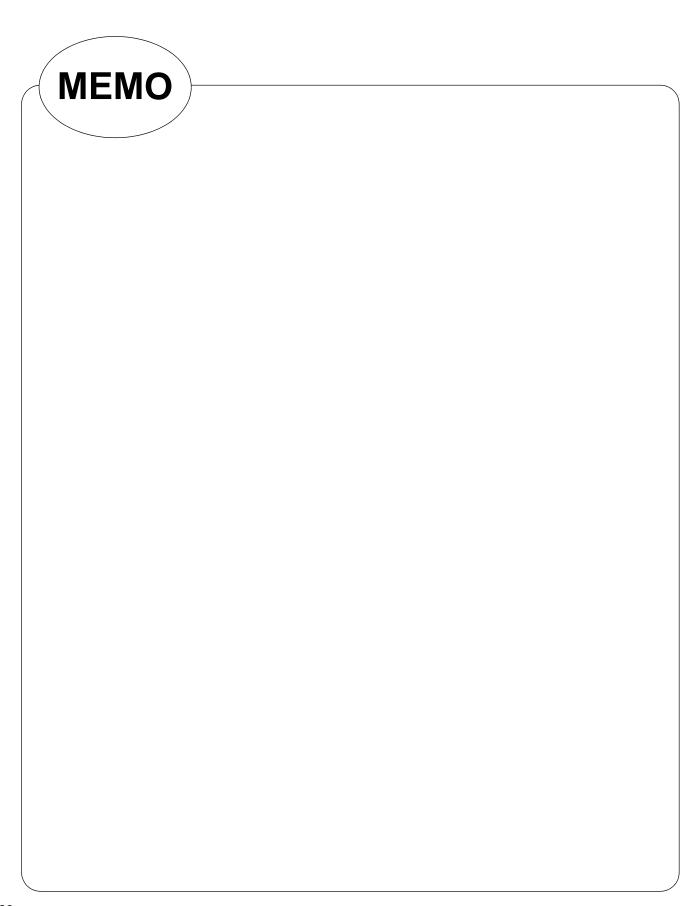


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MEMO	



MEMO	

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